FORM: P'	ΓΟ-1449	9	U.S. DEPARTMENT OF COMMERCE						Atty Docket No: Serial No:			
(REV: 7-	80)		PATENT AND TRADEMARK OFFICE						2000-0719.01/US		Not Assigned	
Applicant:								it:				
INFORMATION DISCLOSURE STATEMENT BY APPLICANT Micron Technology,									Technology, In	ıc.		
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(37 CFR 1.98(b))			(use s	everal	sheets if	necessai	עכ	Septer	September 8, 2003		Not Assigned	
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			"In-situ Barrier Formation for High Reliable W/Barrier/poly-Si Gate Using Denudation of WNX on									
1 <i>1101</i> 1	AO		Polycrystalline Si", Byung Hak Lee et al., R & D Division, LG Semicon Co. Ltd., 1 Hyangjeong-									
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**EXAMINER:** 

Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication with applicant.